

AMENDMENTS TO THE CLAIMS

The following listing of claims replaces all prior listings of claims in the present application.

What is claimed is:

1. **(Currently Amended)** A semiconductor integrated circuit, comprising:
 - a silicon substrate;
 - a silicon epitaxial layer that touches is formed on the surface of said silicon substrate and has a lower resistivity than the resistivity of said silicon substrate;
 - first and second circuit sections formed in said silicon epitaxial layer; and
 - a device isolation region projecting from said silicon substrate up to a surface of each of said first and second circuit sections between said first and second circuit sections.
2. **(Currently Amended)** The semiconductor integrated circuit according to Claim 1, wherein the resistivity of said silicon substrate is between 20 and 100 times the resistivity of said silicon epitaxial layer.
3. **(Currently Amended)** The semiconductor integrated circuit according to Claim 2, wherein the resistivity of said silicon substrate is between 50 and 100 times the resistivity of said silicon epitaxial layer.
4. **(Canceled)**

5. **(Original)** The semiconductor integrated circuit according to Claim 1, wherein a digital circuit is formed on said first circuit section, and an analog circuit is formed on said second circuit section.

6-10. **(Canceled).**